

Day : Tuesday  
Date: 5/18/2004

Time: 16:46:41

# PALM INTRANET

## Inventor Name Search Result

09/822,191

Your Search was:

Last Name = KANAI

First Name = MASAHIRO

Application#	Patent#	Status	Date Filed	Title	Inventor Name 51
<u>60381442</u>	Not Issued	159	05/17/2002	METHOD AND APPARATUS FOR PACKAGING LIGHTWEIGHT OBJECTS	KANAI, MASAHIRO
<u>10779683</u>	Not Issued	019	02/18/2004	NONVOLATILE SEMICONDUCTOR MEMORY DEVICE	KANAI, MASAHIRO
<u>10776173</u>	Not Issued	020	02/12/2004	PROCESSING APPARATUS, EXHAUST PROCESSING PROCESS AND PLASMA PROCESSING PROCESS	KANAI, MASAHIRO
<u>10763126</u>	Not Issued	019	01/22/2004	IMAGE PROCESSING DEVICE, IMAGE PROCESSING METHOD AND SOLID-STATE IMAGE-PICKUP DEVICE	KANAI, MASAHIRO
<u>10763122</u>	Not Issued	019	01/22/2004	IMAGE PROCESSING DEVICE, IMAGE PROCESSING METHOD AND SOLID-STATE IMAGE-PICKUP DEVICE	KANAI, MASAHIRO
<u>10745604</u>	Not Issued	020 1783	12/29/2003 11/8/-	PLASMA-PROCESSING APPARATUS	KANAI, MASAHIRO JFW
<u>10733455</u>	Not Issued	030	12/12/2003	NON-VOLATILE MEMORY DEVICE	KANAI, MASAHIRO
<u>10733452</u>	Not Issued	030	12/12/2003	DEPOSITED-FILM FORMATION APPARATUS, AND DEPOSITED-FILM FORMATION PROCESS	KANAI, MASAHIRO
<u>10656131</u>	Not Issued	020	09/08/2003	DEPOSITED FILM FORMING APPARATUS AND DEPOSITED FILM FORMING METHOD	KANAI, MASAHIRO
<u>10650763</u>	Not Issued	030	08/29/2003	APPARATUS AND METHOD FOR FORMING DEPOSITED FILM	KANAI, MASAHIRO

<u>10650710</u>	Not Issued	020 2812	08/29/2003 438/38	METHOD OF FORMING SILICON NITRIDE DEPOSITED FILM 7	KANAI, MASAHIRO IFW
<u>10625041</u>	Not Issued	030	07/23/2003	APPARATUS FOR MANUFACTURING PHOTOVOLTAIC ELEMENTS	KANAI, MASAHIRO
<u>10320430</u> 200820/36577	Not Issued	030 1703	12/17/2002 118/124	VACUUM-PROCESSING APPARATUS AND METHOD FOR VACUUM-PROCESSING AN OBJECT	KANAI, MASAHIRO IFW
<u>10238789</u>	Not Issued	020	09/11/2002 9	PRODUCTION APPARATUS OF SEMICONDUCTOR LAYER EMPLOYING DC BIAS AND VHF POWER	KANAI, MASAHIRO
<u>10197668</u>	6744106	150	07/18/2002	NON-VOLATILE SEMICONDUCTOR MEMORY DEVICE	KANAI, MASAHIRO
<u>10197646</u>	6654282	150	07/18/2002	NONVOLATILE SEMICONDUCTOR MEMORY DEVICE	KANAI, MASAHIRO
<u>10197643</u>	Not Issued	041	07/18/2002	NON-VOLATILE SEMICONDUCTOR MEMORY DEVICE	KANAI, MASAHIRO
<u>10195543</u> 200309/0623	Not Issued	041 1753	07/16/2002 204/1924	METHOD AND APPARATUS FOR FORMING DEPOSITION FILM, AND METHOD FOR TREATING SUBSTRATE	KANAI, MASAHIRO IFW
<u>10193066</u>	Not Issued	061	07/12/2002	SEMICONDUCTOR DEVICE HAVING A CAPACITANCE DEVICE	KANAI, MASAHIRO
<u>10144720</u> 20020179012	Not Issued	071 1763	05/15/2002 118/715 ↑	FILM FORMING APPARATUS, ELECTRON SOURCE MANUFACTURING APPARATUS, AND MANUFACTURING METHODS USING THE APPARATUSES	KANAI, MASAHIRO IFW
<u>10043601</u>	Not Issued	095	01/09/2002	INK CARTRIDGE FOR INK-JET PRINTING APPARATUS	KANAI, MASAHIRO
<u>09982846</u> 20020090815	Not Issued	041 2813	10/22/2001 438/485	METHOD FOR FORMING A DEPOSITED FILM BY PLASMA CHEMICAL VAPOR DEPOSITION	KANAI, MASAHIRO IFW
<u>09955160</u>	6587381	150	09/19/2001	PROGRAMMING METHOD FOR NON-VOLATILE SEMICONDUCTOR MEMORY	KANAI, MASAHIRO

				DEVICE	
09955158	6587380	150	09/19/2001	PROGRAMMING METHOD FOR NON-VOLATILE SEMICONDUCTOR MEMORY DEVICE	KANAI, MASAHIRO
09949616	6720037	150	09/12/2001	PLASMA PROCESSING METHOD AND APPARATUS	KANAI, MASAHIRO
09912343	6472296	150	07/26/2001	FABRICATION OF PHOTOVOLTAIC CELL BY PLASMA PROCESS	KANAI, MASAHIRO
09911172	6495392	150	07/23/2001	PROCESS FOR PRODUCING A SEMICONDUCTOR DEVICE	KANAI, MASAHIRO
09900043 90020039832	Not Issued	092 2923	07/09/2001 438/485	THIN FILM FORMATION METHOD	KANAI, MASAHIRO JFW
09861520	6531654	150	05/22/2001	SEMICONDUCTOR THIN-FILM FORMATION PROCESS, AND AMORPHOUS SILICON SOLAR-CELL DEVICE	KANAI, MASAHIRO
09844071	6562400	150	04/30/2001	METHOD AND APPARATUS FOR FORMING DEPOSITION FILM, AND METHOD FOR TREATING SUBSTRATE	KANAI, MASAHIRO
09818640	Not Issued	071 PHE3 Emc. Fa. 427/585	03/28/2001	METHOD AND APPARATUS FOR DEPOSITED FILM	KANAI, MASAHIRO JFW
09800724	6667240	150	03/08/2001	METHOD AND APPARATUS FOR FORMING DEPOSITED FILM	KANAI, MASAHIRO
09797566	Not Issued	071	03/05/2001	APPARATUS FOR FORMING DEPOSITED FILM	KANAI, MASAHIRO
09772987	6547922	150	01/31/2001	VACUUM-PROCESSING APPARATUS AND METHOD FOR VACUUM-PROCESSING AN OBJECT	KANAI, MASAHIRO
09771650	6470823	150	01/30/2001	APPARATUS AND METHOD FOR FORMING A DEPOSITED FILM BY MEANS OF PLASMA CVD	KANAI, MASAHIRO
09769328	Not Issued	082	01/26/2001	DEPOSITED-FILM FORMATION APPARATUS, AND DEPOSITED-FILM FORMATION PROCESS	KANAI, MASAHIRO
09767856	6632284	150	01/24/2001	APPARATUS AND METHOD FOR FORMING DEPOSITED FILM	KANAI, MASAHIRO
09754258	6367920	150	01/05/2001	INK CARTRIDGE FOR INK-	KANAI,

				JET RECORDING APPARATUS, AND INK-JET RECORDING APPARATUS	MASAHIRO
09727440	6526910	150	12/04/2000	APPARATUS AND METHOD FOR FORMING A DEPOSITED FILM BY MEANS OF PLASMA CVD	KANAI, MASAHIRO
09722675	6551471	150	11/28/2000	IONIZATION FILM-FORMING METHOD AND APPARATUS	KANAI, MASAHIRO
<del>09678299</del>	Not Issued	<del>161</del>	10/03/2000	METHOD AND DEVICE FOR FORMING SEMICONDUCTOR THIN FILM AND DEVICE FOR FORMING PHOTOVOLTAIC ELEMENT	KANAI, MASAHIRO
09666182	6367502	150	09/21/2000	FLOW CONTROL DEVICE	KANAI, MASAHIRO
09664219	6368944	150	09/18/2000	METHOD OF MANUFACTURING PHOTOVOLTAIC ELEMENT AND APPARATUS THEREFOR	KANAI, MASAHIRO
09649599	6413794	150	08/29/2000	METHOD OF FORMING PHOTOVOLTAIC ELEMENT	KANAI, MASAHIRO
<del>09645036</del>	Not Issued	<del>164</del>	08/24/2000	PROCESS FOR PRODUCING A SEMICONDUCTOR DEVICE	KANAI, MASAHIRO
09625840	6447612	150	07/26/2000	FILM-FORMING APPARATUS FOR FORMING A DEPOSITED FILM ON A SUBSTRATE, AND VACUUM-PROCESSING APPARATUS AND METHOD FOR VACUUM-PROCESSING AN OBJECT	KANAI, MASAHIRO
09588626	6306267	150	06/07/2000	METHOD OF PRODUCING A PHOTOVOLTAIC DEVICE USING A SPUTTERING METHOD	KANAI, MASAHIRO
09578906	6436797	150	05/26/2000	APPARATUS AND METHOD FOR FORMING A DEPOSITED FILM ON A SUBSTRATE	KANAI, MASAHIRO
09478885	Not Issued	061	01/07/2000	APPARATUS AND METHOD FOR PROCESSING A SUBSTRATE, AND APPARATUS AND METHOD FOR FORMING A DEPOSITED FILM ON A SUBSTRATE	KANAI, MASAHIRO
09469797	6576061	150	12/22/1999	APPARATUS AND METHOD	KANAI,

NO

				FOR PROCESSING A SUBSTRATE	MASAHIRO
09312073	Not Issued	041	05/13/1999	INK CARTRIDGE FOR INK- JET PRINTING APPARATUS	KANAI, MASAHIRO

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<b>Search Another: Inventor</b>	KANAI	MASAHIRO	<input type="button" value="Search"/>

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Time: 16:47:12

## Inventor Name Search Result

Your Search was:

Last Name = KANAI

First Name = MASAHIRO

Application#	Patent#	Status	Date Filed	Title	Inventor Name 51
<u>10448112</u>	Not Issued	030	05/30/2003	NON-VOLATILE SEMICONDUCTOR MEMORY DEVICE AND METHOD OF ACTUATING THE SAME	KANAI, MASAHIRO
<u>10446827</u>	Not Issued	030	05/29/2003	NON-VOLATILE SEMICONDUCTOR MEMORY DEVICE AND METHOD OF ACTUATING THE SAME	KANAI, MASAHIRO
<u>10444990</u>	Not Issued	030 1753	05/27/2003 204/299.01	MILLING APPARATUS ?	KANAI, MASAHIRO IFW
<u>10425652</u> 20030194482	Not Issued	041 1763	04/30/2003 427/482	APPARATUS AND METHOD FOR PROCESSING A SUBSTRATE	KANAI, MASAHIRO IFW
<u>10409190</u> 20030192778	Not Issued	030 1753	04/09/2003 204/19212	METHOD OF FORMING DEPOSITED FILM	KANAI, MASAHIRO IFW
<u>10400872</u> 20030190412	Not Issued	094 2512	03/28/2003 438/759	METHOD OF FORMING DEPOSITED FILM	KANAI, MASAHIRO IFW
<u>10385506</u>	Not Issued	030	03/12/2003	NON-VOLATILE SEMICONDUCTOR MEMORY DEVICE	KANAI, MASAHIRO
<u>10377707</u>	Not Issued	030	03/04/2003	NON-VOLATILE SEMICONDUCTOR MEMORY DEVICE	KANAI, MASAHIRO
<u>10377699</u>	6707742	150	03/04/2003	NONVOLATILE SEMICONDUCTOR MEMORY DEVICE	KANAI, MASAHIRO
<u>10373166</u>	Not Issued	030	02/26/2003	NONVOLATILE REGISTER AND SEMICONDUCTOR DEVICE	KANAI, MASAHIRO
<u>10361573</u>	Not Issued	092	02/11/2003	NONVOLATILE SEMICONDUCTOR MEMORY DEVICE	KANAI, MASAHIRO
<u>10356644</u>	6738291	150	02/03/2003	NONVOLATILE	KANAI,

				SEMICONDUCTOR MEMORY DEVICE	MASAHIRO
<i>no Exh</i>	<u>10350019</u> <i>20030709/2003</i>	Not Issued	071 <i>2818</i>	01/24/2003 <i>438/788</i>	METHOD AND APPARATUS FOR IONIZATION FILM FORMATION KANAI, MASAHIRO <i>IFW</i>
<i>NO</i>	<u>10346756</u>	Not Issued	030	01/17/2003	PACKAGING SYSTEM KANAI, MASAHIRO
<i>NO</i>	<u>10193602</u>	Not Issued	061	07/12/2002	SEMICONDUCTOR DEVICE KANAI, MASAHIRO
<i>NO</i>	<u>10157897</u>	Not Issued	030	05/31/2002	NONVOLATILE SEMICONDUCTOR STORAGE DEVICE KANAI, MASAHIRO
<i>NO</i>	<u>10157896</u>	6707720	150	05/31/2002	NONVOLATILE SEMICONDUCTOR STORAGE DEVICE KANAI, MASAHIRO
	<del>10085102</del>	Not Issued	<del>161</del>	03/01/2002	METHOD OF MANUFACTURING PHOTOVOLTAIC ELEMENT AND APPARATUS THEREFOR KANAI, MASAHIRO
<i>the case</i>	<u>09822191</u>	Not Issued	071	04/02/2001	EXHAUST PROCESSING METHOD, PLASMA PROCESSING METHOD AND PLASMA PROCESSING APPARATUS KANAI, MASAHIRO
	<u>09772988</u>	6638359	150	01/31/2001	DEPOSITED FILM FORMING APPARATUS AND DEPOSITED FILM FORMING METHOD KANAI, MASAHIRO
	<u>09772987</u>	6547922	150	01/31/2001	VACUUM-PROCESSING APPARATUS AND METHOD FOR VACUUM-PROCESSING AN OBJECT KANAI, MASAHIRO
<i>NO</i>	<u>08923259</u>	6162988	150	09/04/1997	PHOTOVOLTAIC ELEMENT KANAI, MASAHIRO
	<del>08416468</del>	Not Issued	<del>166</del>	04/04/1995	CONTINUOUS FORMING METHOD FOR FUNCTIONAL DEPOSITED FILMS AND DEPOSITION THEREOF KANAI, MASAHIRO
	<del>08404616</del>	Not Issued	<del>166</del>	03/15/1995	CONTINUOUS FORMING METHOD FOR FUNCTIONAL DEPOSITED FILMS AND DEPOSITION APPARATUS KANAI, MASAHIRO
	<del>08396266</del> <i>f</i>	Not Issued	<del>161</del>	02/28/1995	PROCESS FOR FORMING DEPOSITED FILM USING A GAS PHASE METHOD INVOLVING AT LEAST ONE KANAI, MASAHIRO

				ACTIVATED COMPOUND	
<del>08140971</del>	Not Issued	166	10/25/1993	PROCESS FOR CONTINUOUSLY FORMING A LARGE AREA FUNCTIONAL DEPOSITED FILM BY MICROWAVE PCVD METHOD AND APPARATUS SUITABLE FOR PRACTICING THE SAME	KANAI, MASAHIRO
<del>08116547</del>	Not Issued	161	09/07/1993	METHOD AND APPARATUS FOR CONTINUOUSLY FORMING FUNCTIONAL DEPOSITED FILMS WITH A LARGE AREA BY A MICROWAVE PLASMA CVD METHOD	KANAI, MASAHIRO
<del>08115268</del>	Not Issued	166	09/02/1993	MICROWAVE PLASMA CVD APPARATUS WITH A DEPOSITION CHAMBER HAVING A CIRCUMFERENTIAL WALL COMPRISING A CURVED MOVING SUBSTRATE WEB AND A MICROWAVE APPLICATOR MEANS HAVING A SPECIFIC DIELECTRIC MEMBER ON THE EXTERIOR THEREOF	KANAI, MASAHIRO
<del>08104497</del>	<del>5366554</del>	150	08/10/1993	DEVICE FOR FORMING A DEPOSITED FILM	KANAI, MASAHIRO
<del>08101018</del>	Not Issued	166	08/03/1993	CONTINUOUS FORMING METHOD FOR FUNCTIONAL DEPOSITED FILMS AND DEPOSITION APPARATUS	KANAI, MASAHIRO
<del>08097046</del>	<del>5382531</del>	150	07/27/1993	METHOD FOR CONTINUOUSLY MANUFACTURING A SEMICONDUCTOR DEVICE	KANAI, MASAHIRO
<del>07858410</del>	<del>5266116</del>	150	03/27/1992	GLOW DISCHARGE APPARATUS FOR CONTINUOUSLY MANUFACTURING SEMICONDUCTOR DEVICE COMPRISING GAS GATES WITH SLOTTED ROLLERS	KANAI, MASAHIRO
<del>07834852</del>	Not Issued	166	02/13/1992	PROCESS FOR CONTINUOUSLY FORMING A LARGE AREA FUNCTIONAL	KANAI, MASAHIRO



				DEPOSITED FILM BY MICROWAVE PCVD METHOD AND AN APPARATUS SUITABLE FOR PRACTICING THE SAME	
<u>07825281</u>	<u>5220181</u>	150	01/15/1992	PHOTOVOLTAIC ELEMENT OF JUNCTION TYPE WITH AN ORGANIC SEMICONDUCTOR LAYER FORMED OF A POLYSILANE COMPOUND	KANAI, MASAHIRO
<del><u>07515640</u></del>	Not Issued	<del>166</del>	04/27/1990	PROCESS FOR THE FORMATION OF A POLYCRYSTALLINE SEMICONDUCTOR FILM BY MICROWAVE PLASMA CHEMICAL VAPOR DEPOSITION METHOD	KANAI, MASAHIRO
<u>07273070</u>	<u>5008726</u>	150	11/18/1988	PIN JUNCTION PHOTOVOLTAIC ELEMENT WITH P OR N-TYPE SEMICONDUCTOR LAYER COMPRISING NON-SINGLE CRYSTAL MATERIAL CONTAINING ZN, SE, TE, H IN AN AMOUNT OF 1 TO 4 ATOMIC % AND A DOPANT AND I-TYPE SEMICONDUCTOR LAYER COMPRISING NON-SINGLE CRYSTAL SI(H,F) MATERIAL	KANAI, MASAHIRO
<u>07272926</u>	<u>4926229</u>	150	11/18/1988	PIN JUNCTION PHOTOVOLTAIC ELEMENT WITH P OR N-TYPE SEMICONDUCTOR LAYER COMPRISING NON-SINGLE CRYSTAL MATERIAL CONTAINING ZN, SE, H IN AN AMOUNT OF 1 TO 4 ATOMIC % AND A DOPANT AND I- TYPE SEMICONDUCTOR LAYER COMPRISING NON- SINGLE CRYSTAL SI(H,F) MATERIAL	KANAI, MASAHIRO
<u>07252525</u>	<u>4898118</u>	150	10/03/1988	APPARATUS FOR FORMING FUNCTIONAL DEPOSITED FILM BY MICROWAVE PLASMA CVD PROCESS	KANAI, MASAHIRO
<u>07221761</u>	<u>4851302</u>	150	07/20/1988	FUNCTIONAL ZNSE:H	KANAI,

				DEPOSITED FILMS	MASAHIRO
<u>06831704</u>	<u>4801468</u>	150	02/21/1986	PROCESS FOR FORMING DEPOSITED FILM	KANAI, MASAHIRO
<u>06831460</u>	<u>4778692</u>	150	02/20/1986	PROCESS FOR FORMING DEPOSITED FILM	KANAI, MASAHIRO
<u>06831448</u>	<u>4784874</u>	150	02/20/1986	PROCESS FOR FORMING DEPOSITED FILM	KANAI, MASAHIRO
<del>06829804</del>	Not Issued	<del>166</del>	02/14/1986	PROCESS FOR FORMING DEPOSITED FILM	KANAI, MASAHIRO
<u>06828256</u>	<u>4716048</u>	150	02/11/1986	PROCESS FOR FORMING DEPOSITED FILM	KANAI, MASAHIRO
<u>06753011</u>	<u>4696882</u>	150	07/08/1985	MEMBER HAVING LIGHT RECEIVING LAYER WITH SMOOTHLY INTERCONNECTING NONPARALLEL INTERFACES	KANAI, MASAHIRO
<u>06752920</u>	<u>4696881</u>	150	07/08/1985	MEMBER HAVING LIGHT RECEIVING LAYER WITH SMOOTHLY CONNECTED INTERFACES	KANAI, MASAHIRO
<u>06740901</u>	<u>4705731</u>	150	06/03/1985	MEMBER HAVING SUBSTRATE WITH PROTRUDING SURFACE LIGHT RECEIVING LAYER OF AMORPHOUS SILICON AND SURFACE REFLECTIVE LAYER	KANAI, MASAHIRO
<u>06725751</u>	<u>4705733</u>	150	04/22/1985	MEMBER HAVING LIGHT RECEIVING LAYER AND SUBSTRATE WITH OVERLAPPING SUBPROJECTIONS	KANAI, MASAHIRO
<u>06709888</u>	<u>4675263</u>	150	03/08/1985	MEMBER HAVING SUBSTRATE AND LIGHT-RECEIVING LAYER OF A-SI:GE FILM AND A-SI FILM WITH NON-PARALLEL INTERFACE WITH SUBSTRATE	KANAI, MASAHIRO
<u>06705516</u>	<u>4696884</u>	150	02/26/1985	MEMBER HAVING PHOTOSENSITIVE LAYER WITH SERIES OF SMOOTHLY CONTINUOUS NON-PARALLEL INTERFACES	KANAI, MASAHIRO
<u>06632878</u>	Not	166	07/20/1984	PHOTOCONDUCTIVE	KANAI,

	Issued		MEMBER	MASAHIRO
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<input type="text" value="KANAI"/>	<input type="text" value="MASAHIRO"/>	<input type="button" value="Search"/>

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# PALM INTRANET

## Inventor Name Search Result

Your Search was:

Last Name = KANAI

First Name = MASAHIRO

Application#	Patent#	Status	Date Filed	Title	Inventor Name 51
<u>08697783</u>	5769963	150	08/30/1996	PHOTOVOLTAIC DEVICE	KANAI , MASAHIRO
<u>08657066</u>	5720826	150	05/29/1996	PHOTOVOLTAIC ELEMENT AND FABRICATION <u>PROCESS</u> THEREOF	KANAI , MASAHIRO
<u>08433052</u>	<u>5575855</u>	150	05/03/1995	APPARATUS FOR FORMING A DEPOSITED FILM	KANAI , MASAHIRO
<u>08426629</u>	<u>5527391</u>	150	04/21/1995	METHOD AND APPARATUS CONTINUOUSLY FORMING FUNCTIONAL DEPOSITED FILMS WITH A LARGE AREA BY A MICROWAVE PLASMA CVD METHOD	KANAI , MASAHIRO
<u>08416468</u>	Not Issued	166	04/04/1995	CONTINUOUS FORMING METHOD FOR FUNCTIONAL DEPOSITED FILMS AND DEPOSITION THEREOF	KANAI , MASAHIRO
<u>07989891</u>	Not Issued	166	12/10/1992	DEVICE FOR FORMING A DEPOSITED FILM	KANAI , MASAHIRO
<u>07924001</u>	Not Issued	166	11/20/1992	METHOD AND APPARATUS FOR CONTINUOUSLY FORMING A LARGE AREA FUNCTIONAL DEPOSITED FILM BY MEANS OF MICROWAVE PLASMA CVD PROCESS	KANAI , MASAHIRO
<u>07904904</u>	Not Issued	166	06/23/1992	PROCESS FOR FORMING DEPOSITED FILM	KANAI , MASAHIRO
<u>07882238</u>	<u>5178905</u>	150	05/08/1992	PROCESS FOR THE FORMATION OF A FUNCTIONAL DEPOSITED FILM BY HYDROGEN RADICAL-ASSISTED CVD METHOD UTILIZING	KANAI , MASAHIRO

				HYDROGEN GAS PLASMA IN SHEET-LIKE STATE	
<del>07860211</del>	<del>Not Issued</del>	<del>166</del>	<del>03/27/1992</del>	<del>DEVICE FOR FORMING A DEPOSITED FILM</del>	<del>KANAI, MASAHIRO</del>
<del>07807182</del>	<del>Not Issued</del>	<del>166</del>	<del>12/16/1991</del>	<del>METHOD AND APPARATUS FOR CONTINUOUSLY FORMING FUNCTIONAL DEPOSITED FILMS WITH A LARGE AREA BY A MICROWAVE PLASMA CVD METHOD</del>	<del>KANAI, MASAHIRO</del>
<del>07794051</del>	<del>Not Issued</del>	<del>166</del>	<del>11/19/1991</del>	<del>METHOD FOR CONTINUOUSLY FORMING A FUNCTIONAL DEPOSIT FILM OF LARGE AREA BY MICRO-WAVE PLASMA CVD METHOD</del>	<del>KANAI, MASAHIRO</del>
<del>07792925</del>	<del>Not Issued</del>	<del>166</del>	<del>11/15/1991</del>	<del>MICROWAVE PLASMA CVD APPARATUS WITH A DEPOSITION CHAMBER HAVING A CIRCUMFERENTIAL WALL COMPRISING A CURVED MOVING SUBSTRATE WEB AND A MICROWAVE APPLICATOR MEANS HAVING A SPECIFIC DIELECTRIC MEMBER ON THE EXTERIOR THEREOF</del>	<del>KANAI, MASAHIRO</del>
<del>07784255</del>	<del>Not Issued</del>	<del>166</del>	<del>10/29/1991</del>	<del>METHOD OF CONTINUOUSLY FORMING A LARGE AREA FUNCTIONAL DEPOSITED FILM BY MICROWAVE PCVD AND APPARATUS FOR THE SAME</del>	<del>KANAI, MASAHIRO</del>
07689879	5358987	150	06/12/1992	NEW POLYSILANE COMPOSITIONS	KANAI, MASAHIRO
07685165	5244698	150	04/12/1991	PROCESS FOR FORMING DEPOSITED FILM	KANAI, MASAHIRO
07639410	5126169	150	01/10/1991	PROCESS FOR FORMING A DEPOSITED FILM FROM TWO MUTUALLY REACTIVE ACTIVE SPECIES	KANAI, MASAHIRO
07543499	5130170	150	06/26/1990	A MICROWAVE PCVD METHOD FOR CONTINUOUSLY FORMING A LARGE AREA FUNCTIONAL	KANAI, MASAHIRO

				DEPOSITED FILM USING A CURVED MOVING SUBSTRATE WEB WITH RADIATION OR PROPAGATION OF MICROWAVE ENERGY WITH A DIRECTIVITY IN ONE DIRECTION PERPENDICULAR TO THE DIRECTION OF MICROWAVE PROPAGATION	
<u>07543431</u>	<u>5114770</u>	150	06/26/1990	METHOD FOR CONTINUOUSLY FORMING FUNCTIONAL DEPOSITED FILMS WITH A LARGE AREA BY A MICROWAVE PLASMA CVD METHOD	KANAI, MASAHIRO
<del>07542512</del>	Not Issued	<del>166</del>	06/22/1990	PROCESS FOR CONTINUOUSLY FORMING A LARGE AREA FUNCTIONAL DEPOSITED FILM BY MICROWAVE PCVD METHOD AND AN APPARATUS SUITABLE FOR PRACTICING THE SAME	KANAI, MASAHIRO
<u>07507001</u>	<u>5178904</u>	150	04/10/1990	PROCESS FOR FORMING DEPOSITED FILM FROM A GROUP II THROUGH GROUP VI METAL HYDROCARBON COMPOUND	KANAI, MASAHIRO
<u>07467540</u>	<u>5002617</u>	150	01/19/1990	PIN HETEROJUNCTION PHOTOVOLTAIC ELEMENTS WITH POLYCRYSTAL AlAs (H,F) SEMICONDUCTOR FILM	KANAI, MASAHIRO
<u>07467538</u>	<u>5006180</u>	150	01/19/1990	PIN HETEROJUNCTION PHOTOVOLTAIC ELEMENTS WITH POLYCRYSTAL GAP (H,F) SEMICONDUCTOR FILM	KANAI, MASAHIRO
<u>07467525</u>	<u>5002618</u>	150	01/19/1990	PIN HETEROJUNCTION PHOTOVOLTAIC ELEMENTS WITH POLYCRYSTAL BAS (H,F) SEMICONDUCTOR FILM	KANAI, MASAHIRO
<u>07430246</u>	<u>4998503</u>	150	11/02/1989	APPARATUS FOR FORMING FUNCTIONAL DEPOSITED FILM BY MICROWAVE	KANAI, MASAHIRO

NO  
NO  
NO  
NO

				PLASMA CVD PROCESS	
07399396	4959106	150	08/28/1989	PHOTOVOLTAIC ELEMENT WITH A SEMICONDUCTOR LAYER COMPRISING NON-SINGLE CRYSTAL MATERIAL CONTAINING AT LEAST ZN, SE AND H IN AN AMOUNT OF 1 TO 4 ATOMIC %	KANAI, MASAHIRO
07354856	5038713	150	05/22/1989	MICROWAVE PLASMA TREATING APPARATUS	KANAI, MASAHIRO
<del>07348105</del>	Not Issued	<del>161</del>	04/28/1989	APPARATUS FOR FORMING DEPOSIT FILM	KANAI, MASAHIRO
<del>07338428</del>	Not Issued	<del>166</del>	04/14/1989	PROCESS FOR FORMING DEPOSITED FILM	KANAI, MASAHIRO
07302260	4914052	150	01/27/1989	PROCESS FOR THE FORMATION OF A FUNCTIONAL DEPOSITED FILM CONTAINING GROUPS III AND V ATOMS BY MICROWAVE PLASMA CHEMICAL VAPOR DEPOSITION PROCESS	KANAI, MASAHIRO
07302245	4908330	150	01/27/1989	PROCESS FOR THE FORMATION OF A FUNCTIONAL DEPOSITED FILM CONTAINING GROUP IV ATOMS OR SILICON ATOMS AND GROUP IV ATOMS BY MICROWAVE PLASMA CHEMICAL VAPOR DEPOSITION PROCESS .	KANAI, MASAHIRO
07302243	4908329	150	01/27/1989	PROCESS FOR THE FORMATION OF A FUNCTIONAL DEPOSITED FILM CONTAINING GROUPS II AND VI ATOMS BY MICROWAVE PLASMA CHEMICAL VAPOR DEPOSITION PROCESS	KANAI, MASAHIRO
07298219	4869931	150	01/17/1989	METHOD FOR FORMING DEPOSITED FILMS OF GROUP II-VI COMPOUNDS	KANAI, MASAHIRO
<del>07275619</del>	Not Issued	<del>166</del>	11/25/1988	DEVICE FOR FORMING A DEPOSITED FILM	KANAI, MASAHIRO
07236792	4888062	150	08/26/1988	PIN JUNCTION PHOTOVOLTAIC ELEMENT HAVING I-TYPE	KANAI, MASAHIRO

				SEMICONDUCTOR LAYER COMPRISING NON-SINGLE CRYSTAL MATERIAL CONTAINING AT LEAST ZN, SE AND H IN AN AMOUNT OF 1 TO 4 ATOMIC %	
07226819	5028488	150	08/01/1988	FUNCTIONAL ZNSE1-XTEX: H DEPOSITED FILM	KANAI, MASAHIRO
<del>07222093</del>	Not Issued	<del>166</del>	07/20/1988	PHOTOVOLTAIC ELEMENT WITH A SEMICONDUCTOR LAYER COMPRISING NON- SINGLE CRYSTAL MATERIAL CONTAINING AT LEAST ZN, SE AND H IN AN AMOUNT OF 1 TO 40 ATOMIC %	KANAI, MASAHIRO
<del>07212096</del>	Not Issued	<del>166</del>	06/27/1988	PROCESS FOR FORMING DEPOSITED FILM	KANAI, MASAHIRO
07113414	4772486	150	10/27/1987	PROCESS FOR FORMING A DEPOSITED FILM	KANAI, MASAHIRO
07015951	4800173	150	02/18/1987	PROCESS FOR PREPARING SI OR GE EPITAXIAL FILM USING FLUORINE OXIDANT	KANAI, MASAHIRO
<del>07012367</del>	Not Issued	<del>166</del>	02/09/1987	PROCESS FOR THE PRODUCTION OF FUNCTIONAL CRYSTALLINE FILM	KANAI, MASAHIRO
07003054	4868014	150	01/13/1987	METHOD FOR FORMING THIN FILM MULTI-LAYER STRUCTURE MEMBER	KANAI, MASAHIRO
<del>07003048</del>	Not Issued	<del>166</del>	01/13/1987	DEVICE FOR FORMING DEPOSITED FILM	KANAI, MASAHIRO
06947029	4771015	150	12/29/1986	METHOD FOR PRODUCING AN ELECTRONIC DEVICE HAVING A MULTI-LAYER STRUCTURE	KANAI, MASAHIRO
06946206	4772570	150	12/24/1986	METHOD FOR PRODUCING AN ELECTRONIC DEVICE HAVING A MULTI-LAYER STRUCTURE	KANAI, MASAHIRO
<del>06945580</del>	Not Issued	<del>166</del>	12/23/1986	DEVICE FOR FORMING A DEPOSITED FILM	KANAI, MASAHIRO
06944359	4830890	150	12/22/1986	METHOD FOR FORMING A DEPOSITED FILM FROM A GASEOUS SILANE COMPOUND HEATED ON A SUBSTRATE AND	KANAI, MASAHIRO



				INTRODUCING AN ACTIVE SPECIES THEREWITH	
<u>06943071</u>	<u>4728528</u>	150	12/18/1986	PROCESS FOR FORMING DEPOSITED FILM	KANAI, MASAHIRO
<del>06942806</del>	<del>Not Issued</del>	<del>166</del>	<del>12/22/1986</del>	<del>APPARATUS FOR FORMING DEPOSIT FILM</del>	<del>KANAI, MASAHIRO</del>
<del>06941425</del>	<del>Not Issued</del>	<del>166</del>	<del>12/15/1986</del>	<del>METHOD FOR FORMING DEPOSITED FILMS OF GROUP II-VI COMPOUNDS</del>	<del>KANAI, MASAHIRO</del>
<u>06939229</u>	<u>Not Issued</u>	<u>166</u>	<u>12/08/1986</u>	<u>PROCESS FOR FORMING DEPOSITED FILM</u>	<u>KANAI, MASAHIRO</u>

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## Inventor Name Search Result

Your Search was:

Last Name = KANAI

First Name = MASAHIRO

Application#	Patent#	Status	Date Filed	Title	Inventor Name 51
09337557	6338872	150	06/22/1999	FILM FORMING METHOD	KANAI, MASAHIRO
<del>09294367</del>	Not Issued	<del>161</del>	04/20/1999	PROCESSING APPARATUS, EXHAUST PROCESSING PROCESS AND PLASMA PROCESSING	KANAI, MASAHIRO
09260044	6482668	150	03/02/1999	PROCESS FOR PRODUCING PHOTOVOLTAIC DEVICE	KANAI, MASAHIRO
09258208	6313430	150	02/26/1999	PLASMA PROCESSING APPARATUS AND PLASMA PROCESSING METHOD	KANAI, MASAHIRO
09257027	6530341	150	02/25/1999	DEPOSITION APPARATUS FOR MANUFACTURING THIN FILM	KANAI, MASAHIRO
09080922	6031198	150	05/19/1998	PLASMA PROCESSING METHOD AND APPARATUS	KANAI, MASAHIRO
09038708	6271055	150	03/09/1998	PROCESS FOR MANUFACTURING SEMICONDUCTOR ELEMENT USING NON- MONOCRYSTALLINE SEMICONDUCTOR LAYERS OF FIRST AND SECOND CONDUCTIVITY TYPES AND AMORPHOUS AND MICROCRYSTALLINE I-TYPE SEMICONDUCTORS LAYERS	KANAI, MASAHIRO
09037825	6153823	150	03/11/1998	PHOTOELECTRIC CONVERSION ELEMENT HAVING A SURFACE MEMBER OR A PROTECTION MEMBER AND BUILDING MATERIAL USING THE SAME	KANAI, MASAHIRO

09021987	5928722	150	02/11/1998	METHOD OF TRANSFERRING BONDING AGENT AND TRANSFER APPARATUS	KANAI, MASAHIRO
08927413	6159763	150	09/10/1997	METHOD AND DEVICE FOR FORMING SEMICONDUCTOR THIN FILM, AND METHOD AND DEVICE FOR FORMING PHOTOVOLTAIC ELEMENT	KANAI, MASAHIRO
08844429	6096389	150	04/18/1997	METHOD AND APPARATUS FOR FORMING A DEPOSITED FILM USING A MICROWAVE CVD PROCESS	KANAI, MASAHIRO
08800512	6153013	150	02/14/1997	DEPOSITED-FILM-FORMING APPARATUS	KANAI, MASAHIRO
08782811	5927994	150	01/13/1997	METHOD FOR MANUFACTURING THIN FILM, AND DEPOSITION APPARATUS	KANAI, MASAHIRO
<del>08773907</del>	Not Issued	<del>161</del>	12/27/1996	INSTRUMENT FOR SIMPLIFIED IMMUNOASSAY AND SIMPLIFIED IMMUNOASSAY METHOD USING THE INSTRUMENT	KANAI, MASAHIRO
08768609	6350489	150	12/18/1996	DEPOSITED-FILM FORMING PROCESS AND DEPOSITED-FILM FORMING APPARATUS	KANAI, MASAHIRO
08754066	5968274	150	11/20/1996	CONTINUOUS FORMING METHOD FOR FUNCTIONAL DEPOSITED FILMS AND DEPOSITION APPARATUS	KANAI, MASAHIRO
08741352	5946587	150	10/29/1996	CONTINUOUS FORMING METHOD FOR FUNCTIONAL DEPOSITED FILMS	KANAI, MASAHIRO
08717629	5897332	150	09/23/1996	METHOD FOR MANUFACTURING PHOTOELECTRIC CONVERSION ELEMENT	KANAI, MASAHIRO
08704138	6273955	150	08/28/1996	FILM FORMING APPARATUS AND METHOD	KANAI, MASAHIRO
<del>08697684</del>	Not Issued	<del>161</del>	08/28/1996	PHOTOVOLTAIC CELL AND METHOD OF AND APPARATUS FOR ITS FABRICATION	KANAI, MASAHIRO
08617943	5766349	150	03/15/1996	TRANSFER APPARATUS FOR TRANSFERRING BONDING AGENT	KANAI, MASAHIRO

08610076	5919310	150	02/29/1996	CONTINUOUSLY FILM-FORMING APPARATUS PROVIDED WITH IMPROVED GAS GATE MEANS	KANAI, MASAHIRO
08528330	5629054	150	09/14/1995	METHOD FOR CONTINUOUSLY FORMING A FUNCTIONAL DEPOSIT FILM OF LARGE AREA BY MICROWAVE PLASMA CVD METHOD	KANAI, MASAHIRO
08523169	5589007	150	09/05/1995	PHOTOVOLTAIC ELEMENTS AND PROCESS AND APPARATUS FOR THEIR FORMATION	KANAI, MASAHIRO
08459485	5520740	150	06/02/1995	PROCESS FOR CONTINUOUSLY FORMING A LARGE AREA FUNCTIONAL DEPOSITED FILM BY MICROWAVE PCVD METHOD AND APPARATUS SUITABLE FOR PRACTICING THE SAME	KANAI, MASAHIRO
08450620	5714010	150	05/25/1995	PROCESS FOR CONTINUOUSLY FORMING A LARGE AREA FUNCTIONAL DEPOSITED FILM BY MICROWAVE PCVD METHOD AND AN APPARATUS SUITABLE FOR PRACTICING THE SAME	KANAI, MASAHIRO
08351949	5523126	150	12/08/1994	METHOD OF CONTINUOUSLY FORMING A LARGE AREA FUNCTIONAL DEPOSITED FILM BY MICROWAVE PCVD	KANAI, MASAHIRO
08334032	5468521	150	11/02/1994	METHOD FOR FORMING A PHOTOELECTRIC DEPOSITED FILM	KANAI, MASAHIRO
<del>08262360</del>	Not Issued	<del>166</del>	06/20/1994	METHOD AND APPARATUS FOR CONTINUOUSLY FORMING FUNCTIONAL DEPOSITED FILMS WITH A LARGE AREA BY A MICROWAVE PLASMA CVD METHOD	KANAI, MASAHIRO
08261655	5514217	150	06/07/1994	MICROWAVE PLASMA CVD APPARATUS WITH A DEPOSITION CHAMBER HAVING A	KANAI, MASAHIRO

very large case ↓

				CIRCUMFERENTIAL WALL COMPRISING A CURVED MOVING SUBSTRATE WEB AND A MICROWAVE APPLICATOR MEANS HAVING A SPECIFIC DIELECTRIC MEMBER ON THE EXTERIOR THEREOF	
<del>08255815</del>	Not Issued	166	06/07/1994	METHOD FOR CONTINUOUSLY FORMING A FUNCTIONAL DEPOSIT FILM OF LARGE AREA BY MICRO- WAVE PLASMA CVD METHOD	KANAI, MASAHIRO
08220575	5976257	150	03/31/1994	METHOD AND APPARATUS FOR CONTINUOUSLY FORMING A LARGE AREA FUNCTIONAL DEPOSITED FILM BY MEANS OF MICROWAVE PLASMA CVD PROCESS	KANAI, MASAHIRO
<del>08218834</del>	Not Issued	166	03/28/1994	PROCESS FOR FORMING A DEPOSITED FILM USING A GAS PHASE METHOD INVOLVING AT LEAST ONE ACTIVATED COMPOUND	KANAI, MASAHIRO
<del>08187550</del>	Not Issued	166	01/28/1994	PHOTOVOLTAIC ELEMENTS AND PROCESS AND APPARATUS FOR THEIR FORMATION	KANAI, MASAHIRO
<del>08181478</del>	Not Issued	166	01/14/1994	METHOD OF CONTINUOUSLY FORMING A LARGE AREA FUNCTIONAL DEPOSITED FILM BY MICROWAVE PCVD AND APPARATUS FOR THE SAME	KANAI, MASAHIRO
<del>08091729</del>	Not Issued	166	07/15/1993	METHOD FOR CONTINUOUSLY FORMING A FUNCTIONAL DEPOSIT FILM OF LARGE AREA BY MICRO- WAVE PLASMA CVD METHOD	KANAI, MASAHIRO
<del>07994174</del>	Not Issued	166	12/18/1992	METHOD AND APPARATUS FOR CONTINUOUSLY FORMING FUNCTIONAL DEPOSITED FILMS WITH A LARGE AREA BY A MICROWAVE PLASMA CVD	KANAI, MASAHIRO

				METHOD	
<del>07967238</del>	Not Issued	<del>166</del>	10/27/1992	DEPOSITED FILM FORMING METHOD AND DEPOSITED FILM FORMING APPARATUS	KANAI, MASAHIRO
07943991	5510151	150	09/11/1992	CONTINUOUS FILM-FORMING PROCESS USING MICROWAVE ENERGY IN A MOVING SUBSTRATE WEB FUNCTIONING AS A SUBSTRATE AND A PLASMA GENERATING SPACE	KANAI, MASAHIRO
<del>07690313</del>	Not Issued	<del>166</del>	04/25/1991	PROCESS FOR FORMING DEPOSITED FILM	KANAI, MASAHIRO
<del>07625021</del>	Not Issued	<del>166</del>	12/10/1990	PHOTOVOLTAIC ELEMENT OF JUNCTION TYPE WITH AN ORGANIC SEMICONDUCTOR LAYER FORMED OF A POLYSILANE COMPOUND	KANAI, MASAHIRO
07317653	4971832	150	03/01/1989	HR-CVD PROCESS FOR THE FORMATION OF A FUNCTIONAL DEPOSITED FILM ON A SUBSTRATE WITH APPLICATION OF A VOLTAGE IN THE RANGE OF -5 TO -100 V	KANAI, MASAHIRO
<del>07089758</del>	Not Issued	<del>166</del>	08/27/1987	PROCESS AND APPARATUS FOR FORMING A DEPOSITED FILM	KANAI, MASAHIRO
07061003	4726963	150	06/09/1987	PROCESS FOR FORMING DEPOSITED FILM	KANAI, MASAHIRO
<del>07012367</del>	Not Issued	<del>166</del>	02/09/1987	PROCESS FOR THE PRODUCTION OF FUNCTIONAL CRYSTALLINE FILM	KANAI, MASAHIRO
06739867	4705730	150	05/31/1985	LIGHT-RECEIVING MEMBER	KANAI, MASAHIRO
06726768	4705732	150	04/24/1985	MEMBER HAVING SUBSTRATE WITH PROJECTING PORTIONS AT SURFACE AND LIGHT RECEIVING LAYER OF AMORPHOUS SILICON	KANAI, MASAHIRO
06720011	4701393	150	04/04/1985	MEMBER WITH LIGHT RECEIVING LAYER OF A-SI (GE) AND A-SI AND HAVING PLURALITY OF NON-	KANAI, MASAHIRO

NO

NU

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				PARALLEL INTERFACES	
06719980	4701392	150	04/04/1985	MEMBER HAVING LIGHT RECEIVING LAYER WITH NONPARALLEL INTERFACES AND ANTIREFLECTION LAYER	KANAI, MASAHIRO
06717821	4720443	150	03/29/1985	MEMBER HAVING LIGHT RECEIVING LAYER WITH NONPARALLEL INTERFACES	KANAI, MASAHIRO
06699868	4650736	150	02/08/1985	LIGHT RECEIVING MEMBER HAVING PHOTOSENSITIVE LAYER WITH NON-PARALLEL INTERFACES	KANAI, MASAHIRO

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Your Search was:

Last Name = KANAI

First Name = MASAHIRO

Application#	Patent#	Status	Date Filed	Title	Inventor Name 42
09439609	6602347	150	11/12/1999	APPARATUS AND METHOD FOR PROCESSING A SUBSTRATE	KANAI, MASAHIRO
09425169	6312411	150	10/22/1999	FLUID SUPPLYING APPARATUS ? liquid ? ? gas ?	KANAI, MASAHIRO
09419115	6397775	150	10/15/1999	DEPOSITED FILM FORMING SYSTEM AND PROCESS	KANAI, MASAHIRO
09363825	6287943	150	07/30/1999	DEPOSITION OF SEMICONDUCTOR LAYER BY PLASMA PROCESS	KANAI, MASAHIRO
09358930	6261862	150	07/23/1999	PROCESS FOR PRODUCING PHOTOVOLTAIC ELEMENT	KANAI, MASAHIRO
09110124	6223684	150	07/06/1998	FILM DEPOSITION APPARATUS	KANAI, MASAHIRO
09076238	6093290	150	05/12/1998	METHOD OF GENERATING A RECIPROCATING PLURALITY OF MAGNETIC FLUXES ON A TARGET	KANAI, MASAHIRO
08814081	6113732	150	03/10/1997	DEPOSIT FILM FORMING APPARATUS	KANAI, MASAHIRO
<del>08359817</del>	Not Issued	164	12/20/1994	PHOTOVOLTAIC CELL AND METHOD OF AND APPARATUS FOR ITS FABRICATION	KANAI, MASAHIRO
08305285	5482557	150	09/14/1994	DEVICE FOR FORMING DEPOSITED FILM	KANAI, MASAHIRO
<del>08302221</del>	Not Issued	166	09/07/1994	PROCESS FOR CONTINUOUSLY FORMING A LARGE AREA SUITABLE FOR PRACTICING THE SAME	KANAI, MASAHIRO
08295487	5397395	150	08/25/1994	METHOD OF CONTINUOUSLY FORMING A LARGE AREA FUNCTIONAL DEPOSITED	KANAI, MASAHIRO



NO

				FILM BY MICROWAVE PCVD AND APPARATUS FOR THE SAME	
<u>08271331</u>	<u>5559464</u>	150	07/06/1994	SIGNAL VOLTAGE LEVEL CONVERSION CIRCUIT AND OUTPUT BUFFER CIRCUIT	KANAI, MASAHIRO
<u>08073976</u>	<u>5391232</u>	150	06/08/1993	DEVICE FOR FORMING A DEPOSITED FILM	KANAI, MASAHIRO
<del>08070476</del>	Not Issued	<del>161</del>	10/14/1993	CONTINUOUSLY FILM-FORMING APPARATUS PROVIDED WITH IMPROVED GAS GATE MEANS	KANAI, MASAHIRO
<del>08041511</del>	Not Issued	<del>166</del>	04/01/1993	PROCESS FOR FORMING DEPOSITED FILM	KANAI, MASAHIRO
<del>07999543</del>	Not Issued	<del>166</del>	12/31/1992	MICROWAVE PLASMA VCD APPARATUS WITH A DEPOSITION CHAMBER HAVING A CIRCUMFERENTIAL WALL COMPRISING A CURVED MOVING SUBSTRATE WEB AND A MICROWAVE APPLICATOR MEANS HAVING A SPECIFIC DIELECTRIC MEMBER ON THE EXTERIOR THEREOF	KANAI, MASAHIRO
<u>07800456</u>	<u>5296036</u>	150	11/27/1991	APPARATUS FOR CONTINUOUSLY FORMING A LARGE AREA FUNCTIONAL DEPOSIT FILM INCLUDING MICROWAVE TRANSMISSIVE MEMBER TRANSFER MEANS	KANAI, MASAHIRO
<u>07799900</u>	<u>5192717</u>	150	12/02/1991	PROCESS FOR THE FORMATION OF A POLYCRYSTALLINE SEMICONDUCTOR FILM BY MICROWAVE PLASMA CHEMICAL VAPOR DEPOSITION METHOD	KANAI, MASAHIRO
<del>07769163</del>	Not Issued	<del>166</del>	10/11/1991	DEVICE FOR FORMING A DEPOSITED FILM	KANAI, MASAHIRO
<del>07744820</del>	Not Issued	<del>166</del>	08/12/1991	PROCESS FOR THE FORMATION OF A FUNCTIONAL DEPOSITED FILM BY HYDROGEN RADICAL-ASSISTED CVD METHOD UTILIZING	KANAI, MASAHIRO

				HYDROGEN GAS PLASMA IN SHEET-LIKE STATE	
07469808	5294285	150	01/22/1990	PROCESS FOR THE PRODUCTION OF FUNCTIONAL CRYSTALLINE FILM	KANAI, MASAHIRO
07467537	5007971	150	01/19/1990	PIN HETEROJUNCTION PHOTOVOLTAIC ELEMENTS WITH POLYCRYSTAL BP(H,F) SEMICONDUCTOR FILM	KANAI, MASAHIRO
07467523	5024706	150	01/19/1990	PIN HETEROJUNCTION PHOTOVOLTAIC ELEMENTS WITH POLYCRYSTAL AIP (H,F) SEMICONDUCTOR FILM	KANAI, MASAHIRO
07442511	4951602	150	11/28/1989	MICROWAVE PLASMA CHEMICAL VAPOR DEPOSITION APPARATUS FOR CONTINUOUSLY PREPARING SEMICONDUCTOR DEVICES	KANAI, MASAHIRO
<del>07441224</del>	Not Issued	<del>166</del>	11/27/1989	DEVICE FOR FORMING DEPOSITED FILM	KANAI, MASAHIRO
<del>07439539</del>	Not Issued	<del>166</del>	11/21/1989	PROCESS FOR THE FORMATION OF A FUNCTIONAL DEPOSITED FILM BY HYDROGEN RADICAL-ASSISTED CVD METHOD UTILIZING HYDROGEN GAS PLASMA IN SHEET-LIKE STATE	KANAI, MASAHIRO
06831413	4818563	150	02/20/1986	PROCESS FOR FORMING DEPOSITED FILM	KANAI, MASAHIRO
<del>06831412</del>	Not Issued	<del>166</del>	02/20/1986	PROCESS FOR FORMING DEPOSITED FILM	KANAI, MASAHIRO
06831411	4853251	150	02/20/1986	PROCESS FOR FORMING DEPOSITED FILM INCLUDING CARBON AS A CONSTITUENT ELEMENT	KANAI, MASAHIRO
<del>06829929</del>	Not Issued	<del>166</del>	02/18/1986	PROCESS FOR FORMING DEPOSITED FILM	KANAI, MASAHIRO
<del>06829928</del>	Not Issued	<del>166</del>	02/18/1986	PROCESS FOR FORMING DEPOSITED FILM	KANAI, MASAHIRO
<del>06829791</del>	Not Issued	<del>166</del>	02/14/1986	PROCESS FOR FORMING A DEPOSITED FILM	KANAI, MASAHIRO
06829072	4717586	150	02/13/1986	PROCESS FOR FORMING	KANAI,

				DEPOSITED FILM	MASAHIRO
<del>06828543</del>	Not Issued	<del>166</del>	02/12/1986	PROCESS FOR FORMING DEPOSITED FILM	KANAI, MASAHIRO
06826898	4717585	150	02/06/1986	PROCESS FOR FORMING DEPOSITED FILM	KANAI, MASAHIRO
06815129	4661427	150	12/30/1985	AMORPHOUS SILICON PHOTOCONDUCTIVE MEMBER WITH REDUCED SPIN DENSITY IN SURFACE LAYER	KANAI, MASAHIRO
06786970	4678733	150	10/11/1985	MEMBER HAVING LIGHT RECEIVING LAYER OF A- SI:GE (C, N, O) A-SI/SURFACE ANTIREFLECTION LAYER WITH NONPARALLEL INTERFACES	KANAI, MASAHIRO
06753048	4696883	150	07/08/1985	MEMBER HAVING LIGHT RECEIVING LAYER WITH SMOOTHLY CONNECTED NON- PARALLEL INTERFACES ANDDD SURFACE REFLECTIVE LAYER	KANAI, MASAHIRO
06741300	4705735	150	06/04/1985	MEMBER HAVING SUBSTRATE WITH PROTRUDING SURFACE PORTIONS AND LIGHT RECEIVING LAYER WITH AMORPHOUS SILICON MATRIX	KANAI, MASAHIRO
06740714	4705734	150	06/03/1985	MEMBER HAVING SUBSTRATE WITH IRREGULAR SURFACE AND LIGHT RECEIVING LAYER OF AMORPHOUS SILICON	KANAI, MASAHIRO
06739867	4705730	150	05/31/1985	LIGHT-RECEIVING MEMBER	KANAI, MASAHIRO

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1	L1	18	("5126169" "5468521" "5482557" "5575855" "6031198" "6153013" "615930" "6223684").PN.	USPAT; US-PGPUB ; EPO; JPO; DERWENT; IBM_TDB	2004/05/18 12:00
2	L2	2435 2	((216/67-71,94) or (427/446-456,488-491,523-531,533-540,562-564,569-580) or (204/192.12-192.38,298.07,298.09,298.33,298.41) or (118/723MW-723IR)).CCLS.	USPAT; US-PGPUB ; EPO; JPO; DERWENT; IBM_TDB	2004/05/18 12:10
3	L3	2995	(134/1-1.3).CCLS.	USPAT; US-PGPUB ; EPO; JPO; DERWENT; IBM_TDB	2004/05/18 12:10
4	L4	2697 1	2 or 3	USPAT; US-PGPUB ; EPO; JPO; DERWENT; IBM_TDB	2004/05/18 12:14
5	L5	5939	588/\$.ccls.	USPAT; US-PGPUB ; EPO; JPO; DERWENT; IBM_TDB	2004/05/18 12:15
6	L6	26	4 and 5	USPAT; US-PGPUB ; EPO; JPO; DERWENT; IBM_TDB	2004/05/18 12:16
7	L7	1700 82	(waste exhaust byproduct "by-product" "by product" unreacted adj2 (gas reagent precursor))near3 (treat\$6 process\$4)	USPAT; US-PGPUB ; EPO; JPO; DERWENT; IBM_TDB	2004/05/18 12:29

EAST Search - 09/822,191

	L #	Hits	Search Text	DBs	Time Stamp
8	L8	1153	4 and 7	USPAT; US-PGPUB ; EPO; JPO; DERWENT; IBM_TDB	2004/05/18 12:22
9	L9	1171	6 or 8	USPAT; US-PGPUB ; EPO; JPO; DERWENT; IBM_TDB	2004/05/18 12:23
10	L10	8	6 and 8	USPAT; US-PGPUB ; EPO; JPO; DERWENT; IBM_TDB	2004/05/18 12:23
11	L11	18	6 not 8	USPAT; US-PGPUB ; EPO; JPO; DERWENT; IBM_TDB	2004/05/18 12:24
12	L12	862	8 and (chromium Cr molybdenum Mo.m/c. tungsten W.u/c. V.u/c. vanadium nobium Nb tantalum Ta.m/c. titanium Ti.m/c. zirconium Zr Ha.m/c. hafnium)	USPAT; US-PGPUB ; EPO; JPO; DERWENT; IBM_TDB	2004/05/18 12:28
13	L13	149	8 and((waste exhaust byproduct "by-product" "by product" unreacted adj2 (gas reagent precusor))near3 (treat\$6 process\$4)) same (chromium Cr molybdenum Mo.m/c. tungsten W.u/c. V.u/c. vanadium nobium Nb tantalum Ta.m/c. titanium Ti.m/c. zirconium Zr Ha.m/c. hafnium)	USPAT; US-PGPUB ; EPO; JPO; DERWENT; IBM_TDB	2004/05/18 12:31

	L #	Hits	Search Text	DBs	Time Stamp
14	L14	147	13 not 6	USPAT; US-PGPUB ; EPO; JPO; DERWENT; IBM_TDB	2004/05/18 12:31
15	L15	2	13 and 6	USPAT; US-PGPUB ; EPO; JPO; DERWENT; IBM_TDB	2004/05/18 12:31

Day : Tuesday  
Date: 5/18/2004

Time: 13:37:46

# PALM INTRANET

## Inventor Name Search Result

Your Search was:

Last Name = SHISHIDO

First Name = TAKESHI

Application#	Patent#	Status	Date Filed	Title	Inventor Name 14
<u>10733452</u>	Not Issued	030	12/12/2003 4/27/569	DEPOSITED-FILM FORMATION APPARATUS, AND DEPOSITED-FILM FORMATION PROCESS	SHISHIDO, TAKESHI IFW <i>mine</i>
<u>10656131</u> 20040045504	Not Issued	020 12/64	09/08/2003 118/923 E	DEPOSITED FILM FORMING APPARATUS AND DEPOSITED FILM FORMING METHOD	SHISHIDO, TAKESHI IFW
<u>10650763</u> 20040035941	Not Issued	030 12/62	08/29/2003 4/27/569	APPARATUS AND METHOD FOR FORMING DEPOSITED FILM	SHISHIDO, TAKESHI IFW - T. Meek
<u>10472679</u>	Not Issued	030	09/18/2003	STABLE ASTAXANTHIN-CONTAINING POWDERY COMPOSITIONS AND PROCESS FOR PRODUCING THE SAME	SHISHIDO, TAKESHI
<u>10457513</u>	Not Issued	030	06/10/2003	APPARATUS AND PROCESS FOR FORMING DEPOSITED FILM	SHISHIDO, TAKESHI
<u>10101859</u>	Not Issued	160	03/21/2002	METHOD OF FORMING SILICON-BASED THIN FILM, SILICON-BASED THIN FILM, AND PHOTOVOLTAIC ELEMENT	SHISHIDO, TAKESHI
<u>09822191</u>	Not Issued	071	04/02/2001	EXHAUST PROCESSING METHOD, PLASMA PROCESSING METHOD AND PLASMA PROCESSING APPARATUS	SHISHIDO, TAKESHI
<u>09772988</u>	<u>6638359</u>	150	01/31/2001	DEPOSITED FILM FORMING APPARATUS AND DEPOSITED FILM FORMING METHOD	SHISHIDO, TAKESHI
<u>09771650</u>	<u>6470823</u>	150	01/30/2001	APPARATUS AND METHOD	SHISHIDO,

				FOR FORMING A DEPOSITED FILM BY MEANS OF PLASMA CVD	TAKESHI
09769328 2001/06/22/96	Not Issued	082 1763	01/26/2001 156/34843	DEPOSITED-FILM FORMATION APPARATUS, AND DEPOSITED-FILM FORMATION PROCESS	SHISHIDO, TAKESHI FFW
09767856	6632284	150	01/24/2001	APPARATUS AND METHOD FOR FORMING DEPOSITED FILM	SHISHIDO, TAKESHI
09727440	6526910	150	12/04/2000	APPARATUS AND METHOD FOR FORMING A DEPOSITED FILM BY MEANS OF PLASMA CVD	SHISHIDO, TAKESHI
09509996	6562372	150	04/05/2000	TOCOTRIENOL-CONTAINING POWDER, A PROCESS FOR PREPARING IT AND A TABLET COMPRISING COMPRESSED SAID POWDER INTO A TABLET FORM	SHISHIDO, TAKESHI
08958765	Not Issued	161	10/26/1997	APPARATUS FOR STORING AND SEARCHING INFORMATION RECORDING DISKS AND APPARATUS FOR RECORDING AND/OR REPRODUCING THE DISKS APPLYING THE ABOVE	SHISHIDO, TAKESHI

Inventor Search Completed: No Records to Display.

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Day : Tuesday  
Date: 5/18/2004

Time: 13:38:28

# PALM INTRANET

## Inventor Name Search Result

Your Search was:

Last Name = OKABE

First Name = SHOTARO

Application#	Patent#	Status	Date Filed	Title	Inventor Name 46
<u>10776173</u>	Not Issued	020 2812	02/12/2004 438/-	PROCESSING APPARATUS, EXHAUST PROCESSING PROCESS AND PLASMA PROCESSING PROCESS	OKABE, SHOTARO IFW
<u>10625041</u>	Not Issued	030 1743	07/23/2003 118/118	APPARATUS FOR MANUFACTURING PHOTOVOLTAIC ELEMENTS	OKABE, SHOTARO IFW
<u>10457513</u> 20040011296	Not Issued	030 1762	06/10/2003 428/248/11	APPARATUS AND PROCESS FOR FORMING DEPOSITED FILM	OKABE, SHOTARO IFW - T. Meek
<u>10238789</u> 20030022519	Not Issued	020 1762	09/11/2002 118/112	PRODUCTION APPARATUS OF SEMICONDUCTOR LAYER EMPLOYING DC BIAS AND VHF POWER	OKABE, SHOTARO IFW
<u>10113675</u> 20030104664	Not Issued Allowed	092 2813	04/02/2002 438/485	PROCESS FOR FORMING A SILICON-BASED FILM ON A SUBSTRATE USING A TEMPERATURE GRADIENT ACROSS THE SUBSTRATE AXIS	OKABE, SHOTARO IFW
<del>10101859</del>	Not Issued	<del>160</del>	03/21/2002	METHOD OF FORMING SILICON-BASED THIN FILM, SILICON-BASED THIN FILM, AND PHOTOVOLTAIC ELEMENT	OKABE, SHOTARO
<u>10092617</u> 2003007577	Not Issued Allowed	093 1775	03/08/2002 428/446	SEMICONDUCTOR ELEMENT, AND METHOD OF FORMING SILICON-BASED FILM	OKABE, SHOTARO IFW
<del>10085102</del>	Not Issued	<del>161</del>	03/01/2002	METHOD OF MANUFACTURING PHOTOVOLTAIC ELEMENT AND APPARATUS THEREFOR	OKABE, SHOTARO
<u>09912343</u> (6472296)		150	07/26/2001	FABRICATION OF PHOTOVOLTAIC CELL BY plasma	OKABE, SHOTARO

				PLASMA PROCESS	
09911172	6495392	150	07/23/2001	PROCESS FOR PRODUCING A SEMICONDUCTOR DEVICE	OKABE, SHOTARO
09822191	Not Issued	071	04/02/2001	EXHAUST PROCESSING METHOD, PLASMA PROCESSING METHOD AND PLASMA PROCESSING APPARATUS	OKABE, SHOTARO
09797566 20010039924	Not Issued	071 1703	03/05/2001 11/7/23	APPARATUS FOR FORMING DEPOSITED FILM	OKABE, SHOTARO Ifw
09678299	Not Issued	161	10/03/2000	METHOD AND DEVICE FOR FORMING SEMICONDUCTOR THIN FILM AND DEVICE FOR FORMING PHOTOVOLTAIC ELEMENT	OKABE, SHOTARO
09664219	6368944	150	09/18/2000	METHOD OF MANUFACTURING PHOTOVOLTAIC ELEMENT AND APPARATUS THEREFOR	OKABE, SHOTARO
09645036	Not Issued	164	08/24/2000	PROCESS FOR PRODUCING A SEMICONDUCTOR DEVICE	OKABE, SHOTARO
09594563	6399411	150	06/15/2000	METHOD FOR FORMING NON-SINGLE-CRYSTAL SEMICONDUCTOR THIN FILM, AND METHOD FOR PRODUCING PHOTOVOLTAIC DEVICE	OKABE, SHOTARO
09578906	6436797	150	05/26/2000	APPARATUS AND METHOD FOR FORMING A DEPOSITED FILM ON A SUBSTRATE	OKABE, SHOTARO
09363825	6287943	150	07/30/1999	DEPOSITION OF SEMICONDUCTOR LAYER BY PLASMA PROCESS	OKABE, SHOTARO
09294367	Not Issued	161	04/20/1999	PROCESSING APPARATUS, EXHAUST PROCESSING PROCESS AND PLASMA PROCESSING	OKABE, SHOTARO
09258208	6313430	150	02/26/1999	PLASMA PROCESSING APPARATUS AND PLASMA PROCESSING METHOD	OKABE, SHOTARO
09257027	6530341	150	02/25/1999	DEPOSITION APPARATUS FOR MANUFACTURING THIN FILM	OKABE, SHOTARO
09038708	6271055	150	03/09/1998	PROCESS FOR MANUFACTURING SEMICONDUCTOR ELEMENT	OKABE, SHOTARO

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				USING NON-MONCRYSTALLINE SEMICONDUCTOR LAYERS OF FIRST AND SECOND CONDUCTIVITY TYPES AND AMORPHOUS AND MICROCRYSTALLINE I-TYPE SEMICONDUCTORS LAYERS	
08990915	6159300	150	12/15/1997	APPARATUS FOR FORMING NON-SINGLE-CRYSTAL SEMICONDUCTOR THIN FILM, METHOD FOR FORMING NON-SINGLE-CRYSTAL SEMICONDUCTOR THIN FILM, AND METHOD FOR PRODUCING PHOTOVOLTAIC DEVICE	OKABE , SHOTARO
08927413	6159763	150	09/10/1997	METHOD AND DEVICE FOR FORMING SEMICONDUCTOR THIN FILM, AND METHOD AND DEVICE FOR FORMING PHOTOVOLTAIC ELEMENT	OKABE , SHOTARO
08923259	6162988	150	09/04/1997	PHOTOVOLTAIC ELEMENT	OKABE , SHOTARO
08800512	6153013	150	02/14/1997	DEPOSITED-FILM-FORMING APPARATUS	OKABE , SHOTARO
08782811	5927994	150	01/13/1997	METHOD FOR MANUFACTURING THIN FILM, AND DEPOSITION APPARATUS	OKABE , SHOTARO
08754066	5968274	150	11/20/1996	CONTINUOUS FORMING METHOD FOR FUNCTIONAL DEPOSITED FILMS AND DEPOSITION APPARATUS	OKABE , SHOTARO
08741352	5946587	150	10/29/1996	CONTINUOUS FORMING METHOD FOR FUNCTIONAL DEPOSITED FILMS	OKABE , SHOTARO
08717629	5897332	150	09/23/1996	METHOD FOR MANUFACTURING PHOTOELECTRIC CONVERSION ELEMENT	OKABE , SHOTARO
08697783	5769963	150	08/30/1996	PHOTOVOLTAIC DEVICE	OKABE , SHOTARO
<del>08697684</del>	Not Issued	<del>161</del>	08/28/1996	PHOTOVOLTAIC CELL AND METHOD OF AND APPARATUS FOR ITS FABRICATION	OKABE , SHOTARO

NO

08657066	5720826	150	05/29/1996	PHOTOVOLTAIC ELEMENT AND FABRICATION PROCESS THEREOF	OKABE, SHOTARO
08610076	5919310	150	02/29/1996 ?	CONTINUOUSLY FILM-FORMING APPARATUS PROVIDED WITH IMPROVED GAS GATE MEANS	OKABE, SHOTARO
08523169	5589007	150	09/05/1995	PHOTOVOLTAIC ELEMENTS AND PROCESS AND APPARATUS FOR THEIR FORMATION	OKABE, SHOTARO
<del>08416468</del>	Not Issued	<del>166</del>	04/04/1995	CONTINUOUS FORMING METHOD FOR FUNCTIONAL DEPOSITED FILMS AND DEPOSITION THEREOF	OKABE, SHOTARO
<del>08404616</del>	Not Issued	<del>166</del>	03/15/1995	CONTINUOUS FORMING METHOD FOR FUNCTIONAL DEPOSITED FILMS AND DEPOSITION APPARATUS	OKABE, SHOTARO
<del>08359817</del>	Not Issued	<del>164</del>	12/20/1994	PHOTOVOLTAIC CELL AND METHOD OF AND APPARATUS FOR ITS FABRICATION	OKABE, SHOTARO
<del>08187550</del>	Not Issued	<del>166</del>	01/28/1994	PHOTOVOLTAIC ELEMENTS AND PROCESS AND APPARATUS FOR THEIR FORMATION	OKABE, SHOTARO
<del>08101018</del>	Not Issued	<del>166</del>	08/03/1993	CONTINUOUS FORMING METHOD FOR FUNCTIONAL DEPOSITED FILMS AND DEPOSITION APPARATUS	OKABE, SHOTARO
<del>08070476</del>	Not Issued	<del>161</del>	10/14/1993	CONTINUOUSLY FILM-FORMING APPARATUS PROVIDED WITH IMPROVED GAS GATE MEANS	OKABE, SHOTARO
07208214	4913928	150	06/17/1988 7	MICROWAVE PLASMA CHEMICAL VAPOR DEPOSITION APPARATUS WITH MAGNET ON WAVEGUIDE	OKABE, SHOTARO
06731334	4599971	150	05/06/1985	VAPOR DEPOSITION FILM FORMING APPARATUS	OKABE, SHOTARO
<del>06650164</del>	Not Issued	<del>166</del>	09/13/1984	PLASMA VAPOR DEPOSITION FILM FORMING APPARATUS	OKABE, SHOTARO
06647608	4545328	150	09/06/1984	PLASMA VAPOR DEPOSITION FILM FORMING APPARATUS	OKABE, SHOTARO

06647607	4539934	150	09/06/1984	PLASMA VAPOR DEPOSITION FILM FORMING APPARATUS	OKABE, SHOTARO
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Inventor Search Completed: No Records to Display.

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OKABE	SHOTARO	Search

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1	L1	182	("6720037") or ("6472296") or ("6495392") or ("6531654") or ("6562400") or ("6667240") or ("6547922") or ("6470823") or ("6632284") or ("6526910") or ("6551471") or ("6367502") or ("6447612") or ("6306267") or ("6436797") or ("6576061") or ("6638359") or ("6547922") or ("5366554") or ("5382531") or ("5266116") or ("4898118") or ("4801468") or ("4778692") or ("4784874") or ("5575855") or ("5527391") or ("5178905") or ("5244698") or ("5130170") or ("5114770") or ("4998503") or	USPAT; US-PGPUB ; EPO; JPO; DERWENT; IBM_TDB	2004/05/19 11:42
2	L2	1700 82	(waste exhaust byproduct "by-product" "by product" unreacted adj2 (gas reagent precursor))near3 (treat\$6 process\$4)	USPAT; US-PGPUB ; EPO; JPO; DERWENT; IBM_TDB	2004/05/19 11:45
3	L3	7	1 and 2	USPAT; US-PGPUB ; EPO; JPO; DERWENT; IBM_TDB	2004/05/19 11:44

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	L #	Hits	Search Text	DBs	Time Stamp
4	L4	0	<del>1 and (waste exhaust byproduct "by-product" "by product" unreacted adj2 (gas reagent precursor))near3 (treat\$6 process\$4) not 3</del>	USPAT; US-PGPUB ; EPO; JPO; DERWENT; IBM_TDB	2004/05/19 11:45



	L #	Hits	Search Text	DBs	Time Stamp
4	L3	7	1 and 2	USPAT; US-PGPUB ; EPO; JPO; DERWENT; IBM_TDB	2004/05/19 11:46
5	L5	7	<del>1 and (waste exhaust byproduct "by-product" "by product" unreacted adj2 (gas reagent precursor)) near3 (treat\$6 process\$4)</del>	<del>USPAT; US-PGPUB ; EPO; JPO; DERWENT; IBM_TDB</del>	<i>gof</i> 2004/05/19 12:13
6	L6	80	1 and (waste exhaust byproduct "by-product" "by product" unreacted adj2 (gas reagent precursor)) not 3	USPAT; US-PGPUB ; EPO; JPO; DERWENT; IBM_TDB	2004/05/19 12:14